

Title (en)
PROCESS FOR PRODUCTION OF MULTICRYSTAL SILICON AND FACILITY FOR PRODUCTION OF MULTICRYSTAL SILICON

Title (de)
VERFAHREN ZUR HERSTELLUNG VON MULTIKRISTALLINEM SILICIUM UND ANLAGE ZUR HERSTELLUNG VON MULTIKRISTALLINEM SILICIUM

Title (fr)
PROCÉDÉ DE PRODUCTION DE SILICIUM POLYCRISTALLIN ET INSTALLATION DE PRODUCTION DE SILICIUM POLYCRISTALLIN

Publication
EP 2070871 B1 20160217 (EN)

Application
EP 07830677 A 20071026

Priority

- JP 2007070943 W 20071026
- JP 2006308477 A 20061114
- JP 2007273546 A 20071022

Abstract (en)
[origin: EP2070871A1] A method for producing polycrystalline silicon, including: reacting trichlorosilane and hydrogen to produce silicon and a remainder including monosilanes (formula: SiH_n Cl_{4-n}, wherein n is 0 to 4) containing silicon tetrachloride, and a polymer including at least trisilanes or tetrasilanes; and supplying the remainder and hydrogen to a conversion reactor and heating at a temperature within the range of 600 to 1,400°C to convert silicon tetrachloride into trichlorosilane and the polymer into monosilanes.

IPC 8 full level
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CPC (source: EP KR US)
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Cited by
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DE IT

DOCDB simple family (publication)
EP 2070871 A1 20090617; EP 2070871 A4 20130417; EP 2070871 B1 20160217; JP 2008143774 A 20080626; JP 5435188 B2 20140305; KR 101426099 B1 20140801; KR 20090079871 A 20090722; TW 200918450 A 20090501; TW I436946 B 20140511; US 2010160591 A1 20100624; US 8017099 B2 20110913; WO 2008059706 A1 20080522

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